SOT-23 Plastic-Encapsulate Transistors

MMBTA92 TRANSISTOR (NPN)

FEATURES
High breakdown voltage
Complementary to MMBTA42

MARKING:2D

MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-300	V
VCEO	Collector-Emitter Voltage	-300	V
VEBO	Emitter-Base Voltage	-5	V
IC	Collector Current -Continuous	-0.3	A
PC	Collector Power Dissipation	0.3	W
Tj	Junction Temperature	150	℃
Tstg	Storage Temperature	-55-150	℃

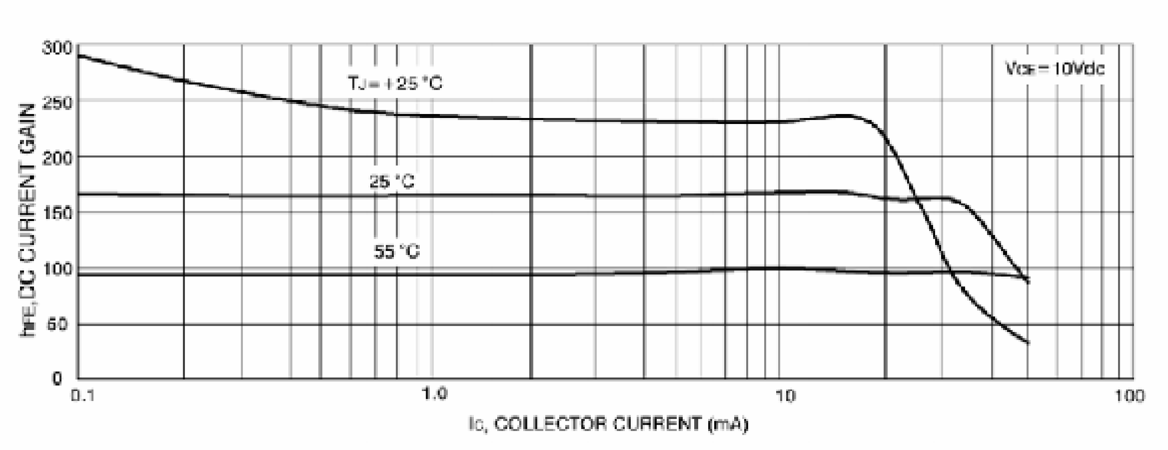
ELECTRICAL CHARACTERISTICS (Tamb=25℃unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC= -100μA, IE=0	-300			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= -1mA, IB=0	-300			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-200 V , IE=0			-1	μ A
Collector cut-off current	ICEO	VCE=-200V , IB=0			-10	μ A
Emitter cut-off current	IEBO	VEB=-5V , IC=0			-1	μ A
DC current gain	hFE	VCE=-10V, IC= -10mA	100		300	
Collector-emitter saturation voltage	VCE(sat)	IC=-20mA, IB= -2mA			-0.2	V
Base-emitter saturation voltage	VBE(sat)	IC=-20mA, IB= -2mA			-0.9	V

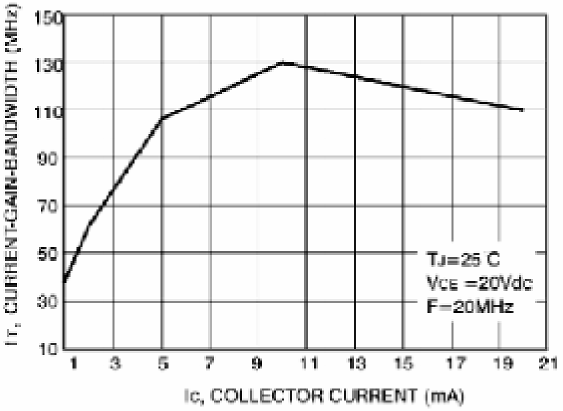
CLASSIFICATION OF hFE

Range	100-200	200-300		

Typical Characteristics



DC Current Gain



Current–Gain — Bandwidth